

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

# TLP504A, TLP504A-2

PROGRAMMABLE CONTROLLERS

AC/DC-INPUT MODULE

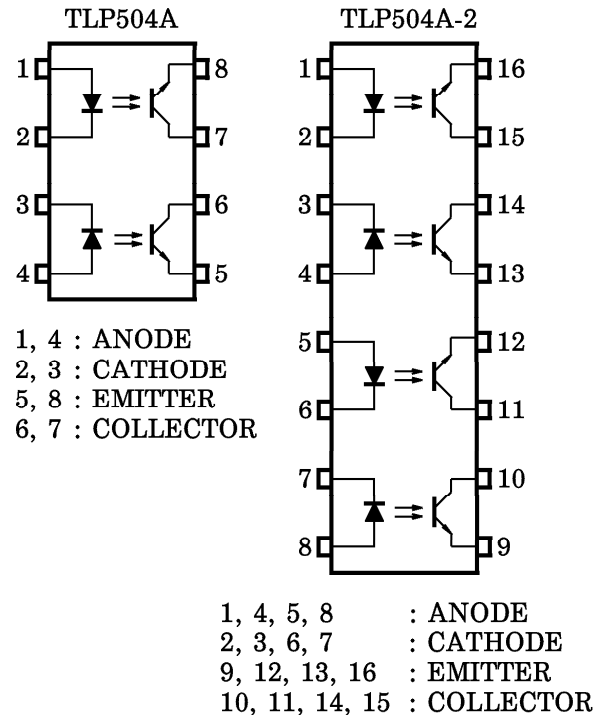
SOLID STATE RELAY

The TOSHIBA TLP504A and TLP504A-2 consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode.

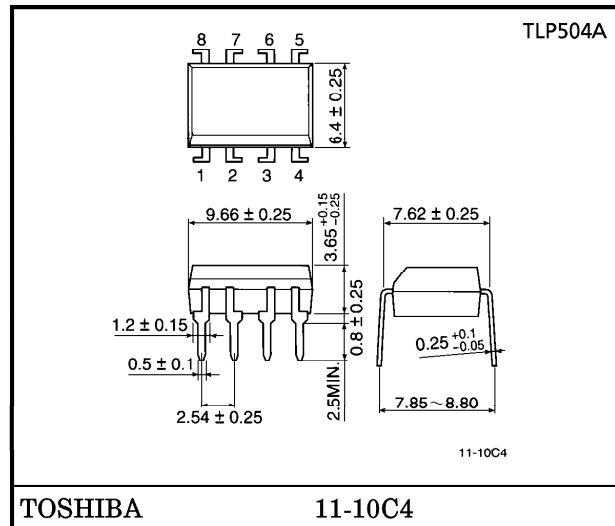
The TLP504A offers two isolated channels in a eight lead plastic DIP package, while the TLP504A-2 provides four isolated channels in a sixteen plastic DIP package.

- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)  
Rank GB : 100% (Min.)
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577,  
File No. E67349

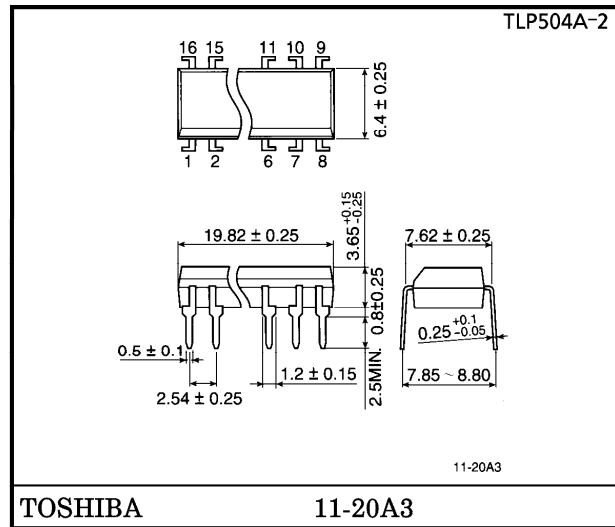
PIN CONFIGURATIONS (TOP VIEW)



Unit in mm



Weight : 0.54g



Weight : 1.1g

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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING		UNIT
			TLP504A	TLP504A-2	
LED	Forward Current	$I_F$	60	50	mA
	Forward Current Derating	$\Delta I_F / ^\circ C$	-0.7 (Ta $\geq$ 39°C)	-0.5 (Ta $\geq$ 25°C)	mA / °C
	Pulse Forward Current	$I_{FP}$	1 (100 $\mu$ s pulse, 100pps)		A
	Reverse Voltage	$V_R$	5		V
	Junction Temperature	$T_j$	125		°C
DETECTOR	Collector-Emitter Voltage	$V_{CEO}$	55		V
	Emitter-Collector Voltage	$V_{ECO}$	7		V
	Collector Current	$I_C$	50		mA
	Collector Power Dissipation (1 Circuit)	$P_C$	150	100	mW
	Collector Power Dissipation Derating (1 Circuit Ta $\geq$ 25°C)	$\Delta P_C / ^\circ C$	-1.5	-1.0	mW / °C
	Junction Temperature	$T_j$	125		°C
Storage Temperature Range		$T_{stg}$	-55~150		°C
Operating Temperature Range		$T_{opr}$	-55~100		°C
Lead Soldering Temperature		$T_{sol}$	260 (10s)		°C
Total Package Power Dissipation		$R_T$	250	150	mW
Total Package Power Dissipation Derating (Ta $\geq$ 25°C)		$\Delta P_T / ^\circ C$	-2.5	-1.5	mW / °C
Isolation Voltage		$BV_S$	2500 (AC, 1min., R.H. $\leq$ 60%) (Note 1)		Vrms

(Note 1) Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	$V_{CC}$	—	5	24	V
Forward Current	$I_F$	—	16	20	mA
Collector Current	$I_C$	—	1	10	mA
Operating Temperature	$T_{opr}$	-25	—	85	°C

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- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
- The products described in this document are subject to foreign exchange and foreign trade control laws.
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## INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	$V_F$	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	$I_R$	$V_R = 5\text{V}$	—	—	10	$\mu\text{A}$
	Capacitance	$C_T$	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	$I_{CEO}$	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	$\mu\text{A}$
Capacitance Collector to Emitter	$C_{CE}$	$V = 0, f = 1\text{MHz}$	—	10	—	pF	

## COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	$I_C / I_F$	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F(\text{sat})$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$	—	—	0.4	V
		$I_C = 0.2\text{mA}, I_F = 1\text{mA}$ Rank GB	—	0.2	—	
			—	—	0.4	

## ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance Input to Output	$C_S$	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance	$R_S$	$V_S = 500\text{V}$	$5 \times 10^{10}$	$10^{14}$	—	$\Omega$
Isolation Voltage	$BV_S$	AC, 1 minute	2500	—	—	$V_{\text{rms}}$
		AC, 1 second, in oil	—	5000	—	
		DC, 1 minute, in oil	—	5000	—	Vdc

SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	$t_r$	$V_{CC} = 10V, I_C = 2mA$ $R_L = 100\Omega$	—	2	—	$\mu s$
Fall Time	$t_f$		—	3	—	
Turn-on Time	$t_{on}$		—	3	—	
Turn-off Time	$t_{off}$		—	3	—	
Turn-on Time	$t_{ON}$	$R_L = 1.9k\Omega$ (Fig.1) $V_{CC} = 5V, I_F = 16mA$	—	2	—	$\mu s$
Storage Time	$t_s$		—	15	—	
Turn-off Time	$t_{OFF}$		—	25	—	

Fig.1 Switching Time Test Circuit

